

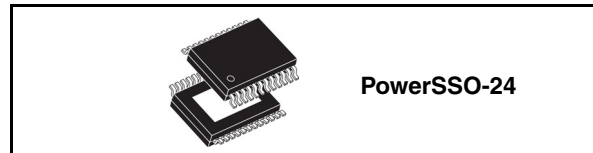
Quad high side smart power solid state relay

Features

Type	$V_{\text{demag}}^{(1)}$	$R_{\text{DSon}}^{(1)}$	$I_{\text{out}}^{(1)}$	V_{CC}
VNI4140K	$V_{\text{CC}}-41 \text{ V}$	0.08Ω	0.7 A	41 V

1. Per channel

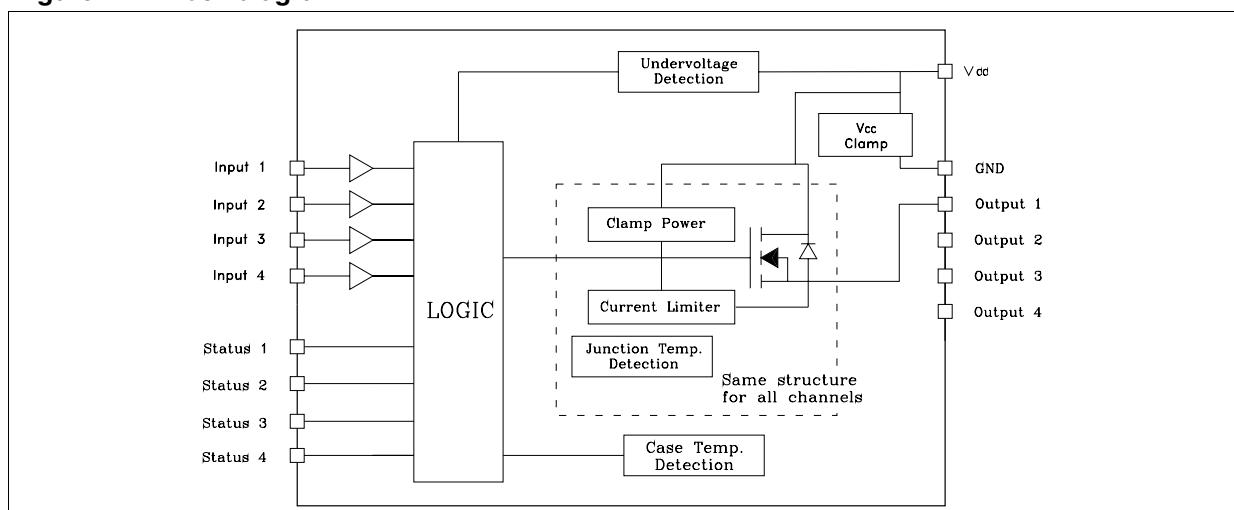
- Output current: 0.7 A per channel
- Shorted load protections
- Junction over-temperature protection
- Case overtemperature protection for thermal independence of the channels
- Thermal case shut-down restart not simultaneous for the various channels
- Protection against loss of ground
- Current limitation
- Undervoltage shut-down
- Open drain diagnostic outputs
- 3.3 V CMOS/TTL compatible inputs
- Fast demagnetization of inductive loads
- Conforms to IEC 61131-2



Description

The VNI4140K is a monolithic device made using STMicroelectronics VIPower technology, intended for driving four independent resistive or inductive loads with one side connected to ground. Active current limitation avoids dropping the system power supply in case of shorted load. Built-in thermal shut-down protects the chip from overtemperature and short circuit. In overload condition, channel turns OFF and back ON automatically so as to maintain junction temperature between T_{TSD} and T_{R} . If this condition makes case temperature reach T_{CSD} , overloaded channel is turned OFF and will restart only when case temperature has decreased down to T_{CR} . In case of more than one channel in overload, re-start of the overloaded channels will not be simultaneous, in order to avoid high peak current from the supply. Non overloaded channels continue to operate normally. The open drain diagnostics outputs indicates over-temperature conditions.

Figure 1. Block diagram



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1 Pin connection

Figure 2. Pin connection (top view)

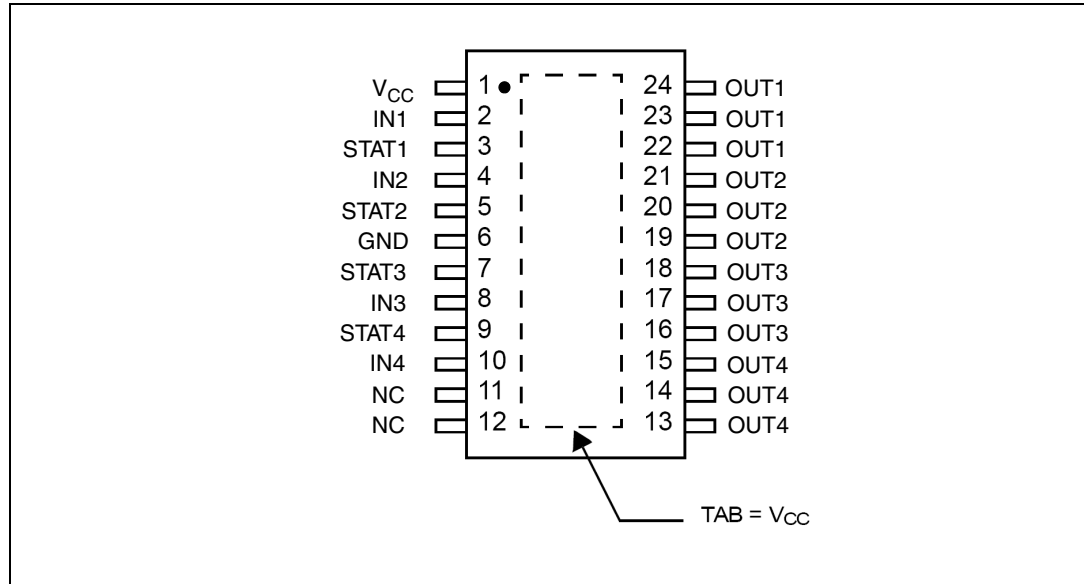


Table 1. Pin description

Pin	Name	Description
Tab	TAB	Exposed tab internally connected to Vcc
1	Vcc	Supply voltage
2	IN1	Channel 1 input 3.3 V CMOS/TTL compatible
3	STAT1	Channel 1 status in open drain configuration
4	IN2	Channel 2 input 3.3 V CMOS/TTL compatible
5	STA2	Channel 2 status in open drain configuration
6	GND	Device ground connection
7	STAT3	Channel 3 status in open drain configuration
8	IN3	Channel 3 input 3.3 V CMOS/TTL compatible
9	STAT4	Channel 4 status in open drain configuration
10	IN4	Channel 4 input 3.3 V CMOS/TTL compatible
11	NC	
12	NC	
13	OUT4	Channel 4 power stage output, internally protected
14	OUT4	Channel 4 power stage output, internally protected
15	OUT4	Channel 4 power stage output, internally protected
16	OUT3	Channel 3 power stage output, internally protected
17	OUT3	Channel 3 power stage output, internally protected

Table 1. Pin description (continued)

Pin	Name	Description
18	OUT3	Channel 3 power stage output, internally protected
19	OUT2	Channel 2 power stage output, internally protected
20	OUT2	Channel 2 power stage output, internally protected
21	OUT2	Channel 2 power stage output, internally protected
22	OUT1	Channel 1 power stage output, internally protected
23	OUT1	Channel 1 power stage output, internally protected
24	OUT1	Channel 1 power stage output, internally protected

2 Maximum ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CC}	Power supply voltage	41	V
$-V_{CC}$	Reverse supply voltage	-0.3	V
I_{GND}	DC ground reverse current	-250	mA
I_{OUT}	Output current (continuous)	Internally limited	A
I_R	Reverse output current (per channel)	-5	A
I_{IN}	Input current (per channel)	± 10	mA
V_{IN}	Input voltage	$+V_{CC}$	V
V_{STAT}	Status pin voltage	$+V_{CC}$	V
I_{STAT}	Status pin current	± 10	mA
V_{ESD}	Electrostatic discharge (R = 1.5 k Ω ; C = 100 pF)	2000	V
E_{AS}	Single pulse avalanche energy per channel not simultaneously	300	mJ
P_{TOT}	Power dissipation at $T_c = 25\text{ }^\circ\text{C}$	Internally limited	W
T_J	Junction operating temperature	Internally limited	$^\circ\text{C}$
T_{STG}	Storage temperature	-55 to 150	$^\circ\text{C}$

2.1 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{th(JC)}$	Thermal resistance junction-case ⁽¹⁾	Max 2	$^\circ\text{C}/\text{W}$
$R_{th(JA)}$	Thermal resistance junction-ambient	Max see Figure 11	$^\circ\text{C}/\text{W}$

1. Per channel

3 Electrical characteristics

(10.5 V < V_{CC} < 36 V; -25 °C < T_J < 125 °C; unless otherwise specified)

Table 4. Power section

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
V _{CC}	Supply voltage		10.5		36	V
R _{DS(on)}	On state resistance	I _{OUT} = 0.5 A at T _J = 25 °C I _{OUT} = 0.5 A			0.080 0.140	Ω Ω
V _{clamp}		I _S = 20 mA	41	45	52	V
I _S	Supply current	All channel in OFF state ON state with V _{IN} = 5 V (T _J = 125 °C)		250 2.4	4	μA mA
V _{OUT(OFF)}	OFF state output voltage	V _{IN} = 0 V and I _{OUT} = 0 A			1	V
I _{OUT(OFF)}	OFF state output current	V _{IN} = V _{OUT} = 0 V	0		5	μA
F _{CP}	Charge pump frequency	Channel in ON state ⁽¹⁾		1450		kHz

1. To cover EN55022 class A and class B normative

Table 5. Switching (V_{CC} = 24 V; -25 °C < T_J < 125 °C, R_L = 48 Ω, input rise time < 0.1 μs)

Symbol	Parameter	Test condition	Min	Typ	Max	Unit
t _{d(ON)}	Turn ON delay			20		μS
t _r	Rise time			10		μS
t _{d(OFF)}	Turn OFF			30		μS
t _f	Fall time			8		μS
dV/dt _(ON)	Turn ON voltage slope			3		V/μS
dV/dt _(off)	Turn OFF voltage slope			4		V/μS

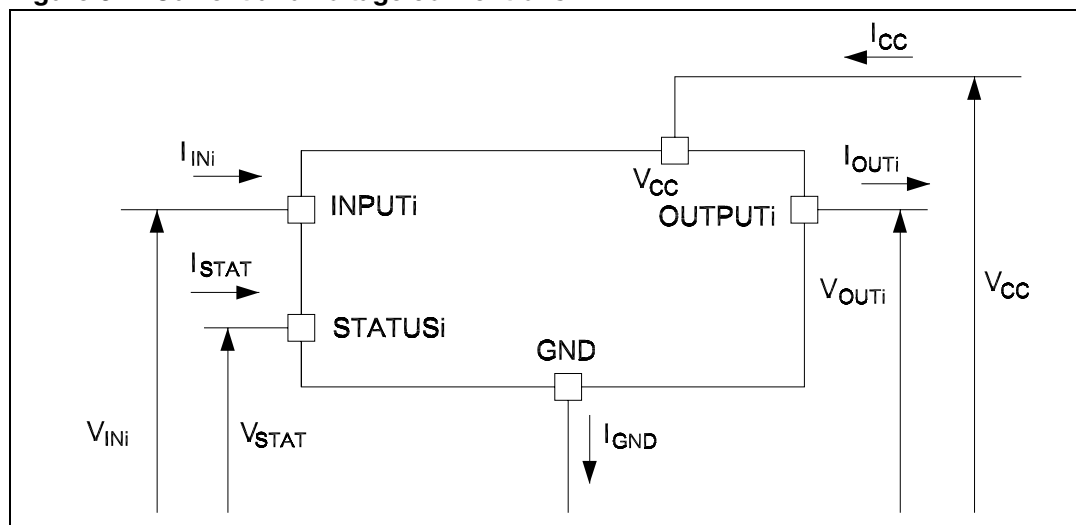
Table 6. Logical input

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage				0.8	V
V_{IH}	Input high level voltage		2.20			V
$V_{I(HYST)}$	Input hysteresis voltage			0.15		V
I_{IN}	Input current	$V_{IN} = 15\text{ V}$			10	μA
		$V_{IN} = 36\text{ V}$			210	

Table 7. Protection and diagnostic

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V_{STAT}	Status voltage output low	$I_{STAT} = 1.6\text{ mA}$			0.6	V
V_{USD}	Undervoltage protection		7		10.5	V
V_{USDHYS}	Undervoltage hysteresis		0.4	0.5		V
I_{LIM}	DC short circuit current	$V_{CC} = 24\text{ V}; R_{LOAD} < 10\text{ m}\Omega$	0.7	1	1.7	A
I_{PEAK}	Maximum DC output Current	Dynamic load		1.3		A
Hyst	Traking limits			0.2		A
I_{LSTAT}	Status leakage current	$V_{CC} = V_{STAT} = 36\text{ V}$		30		μA
T_{TSD}	Junction shut down temperature		150	170	190	$^{\circ}\text{C}$
T_R	Junction reset temperature		135			$^{\circ}\text{C}$
T_{HIST}	Junction thermal hysteresis		7	15		$^{\circ}\text{C}$
T_{CSD}	Case shut-down temperature		125	130	135	$^{\circ}\text{C}$
T_{CR}	Case reset temperature		110			$^{\circ}\text{C}$
T_{CHYST}	Case thermal hysteresis		7	15		$^{\circ}\text{C}$
V_{demag}	Output voltage at turn-OFF	$I_{OUT} = 0.5\text{ A}; L_{LOAD} \geq 1\text{ mH}$	$V_{CC} - 41$	$V_{CC} - 45$	$V_{CC} - 52$	V

Figure 3. Current and voltage conventions



4 Truth table

Table 8. Truth table

	INPUTn	OUTPUTn	STATUSn
Normal operation	L	L	H
	H	H	H
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Shorted load (Current limitation)	L	L	H
	H	X	H

5 Typical application circuit

Figure 4. Typical application circuit

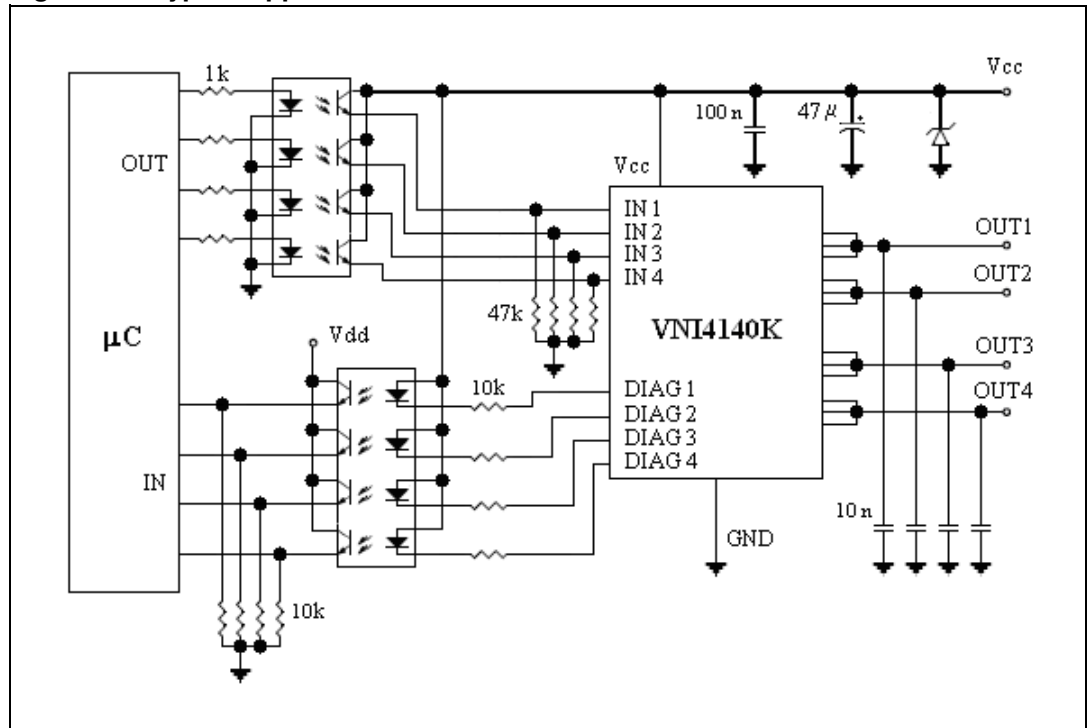
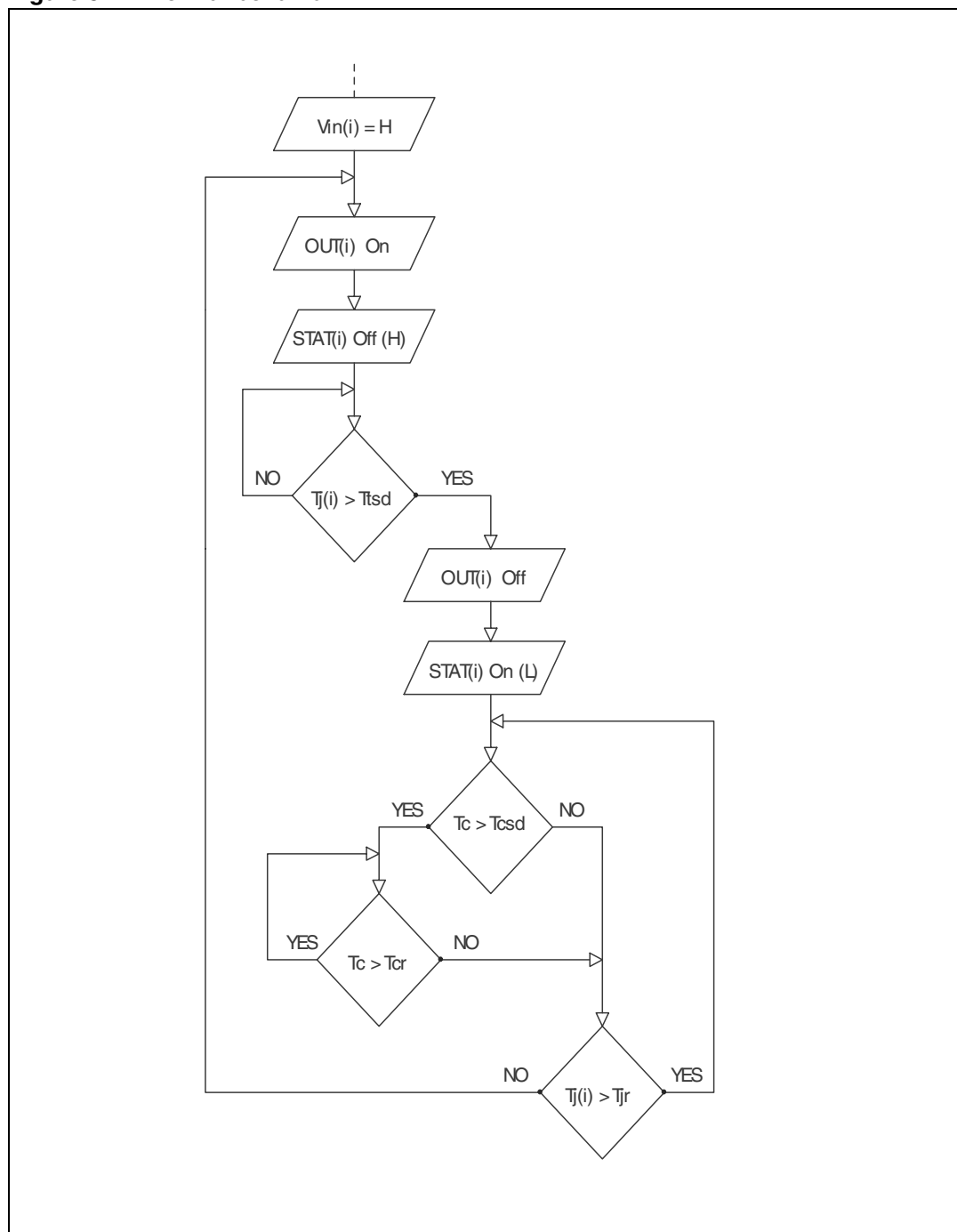
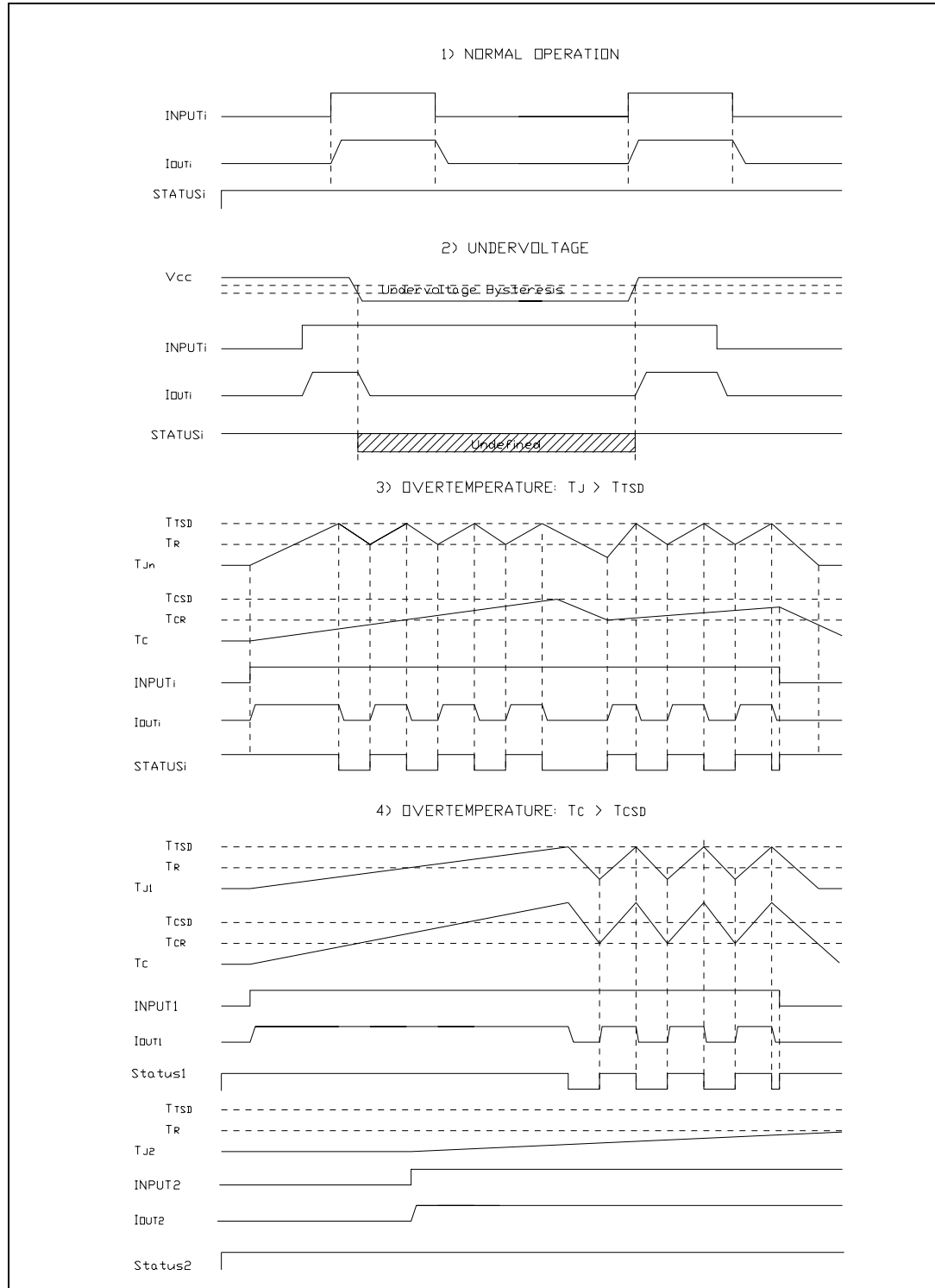


Figure 5. Thermal behavior



6 Switching waveforms

Figure 6. Switching waveforms



7 Pin functions

Figure 7. Input circuit

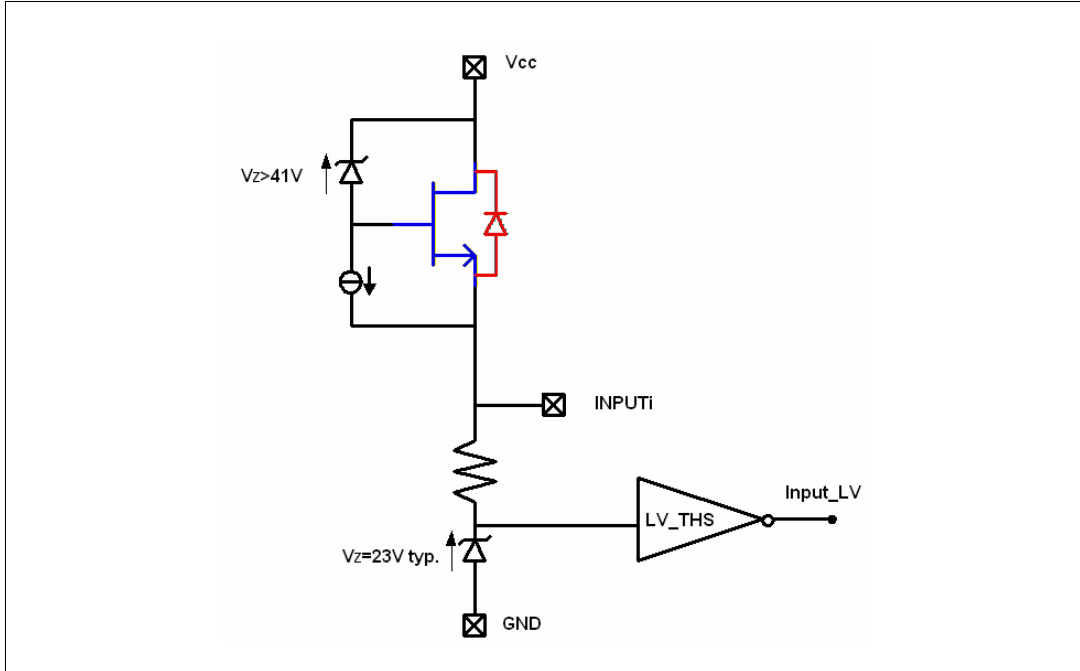


Figure 8. Status circuits

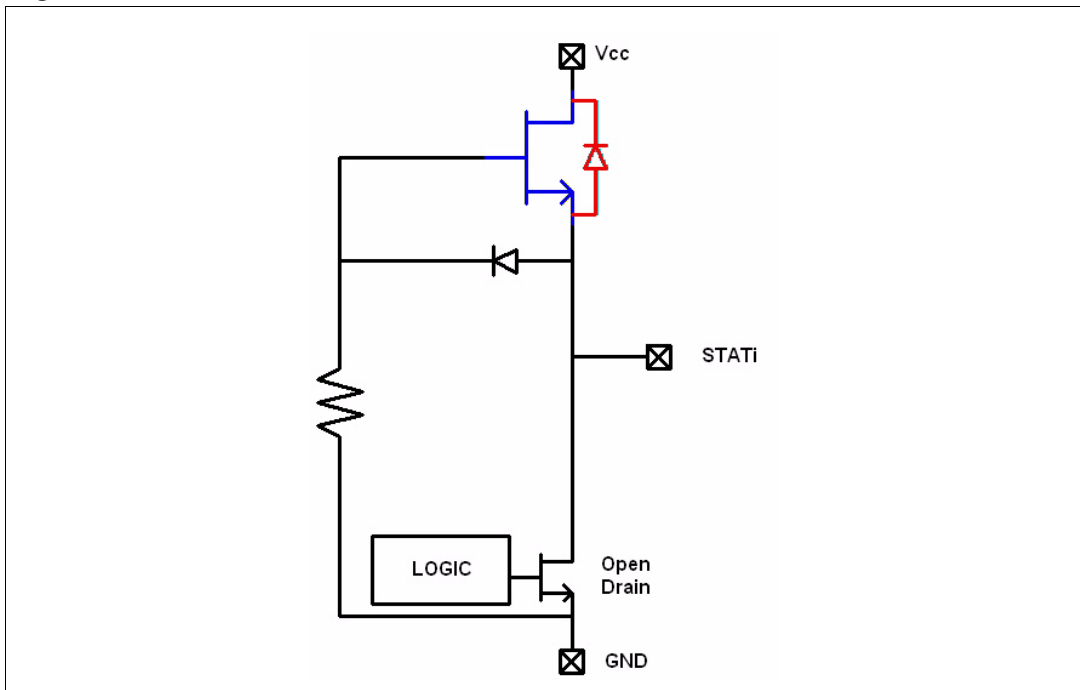
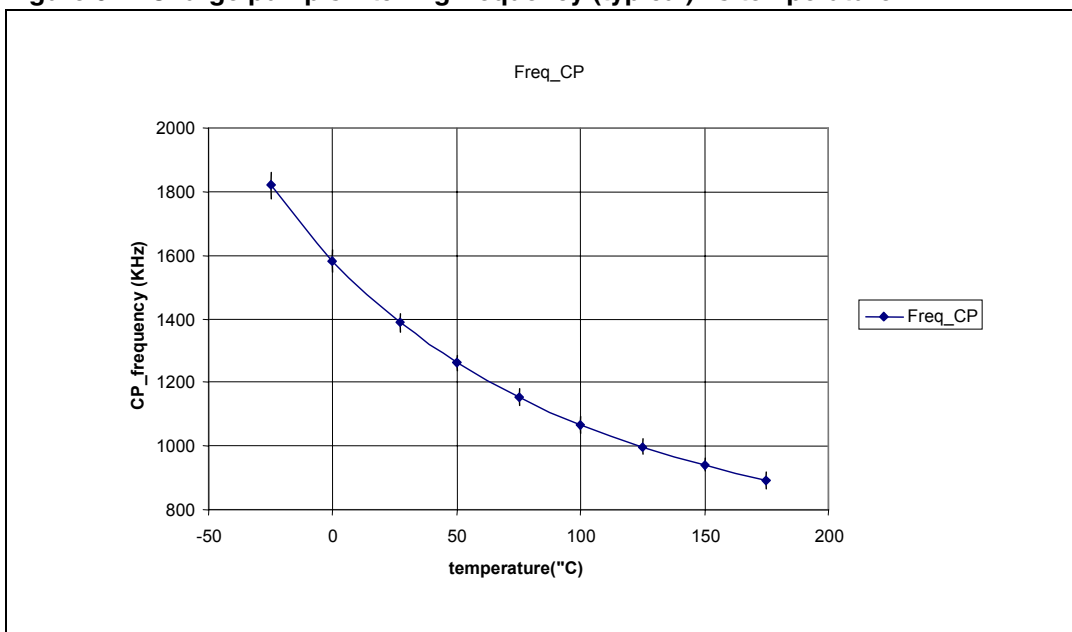


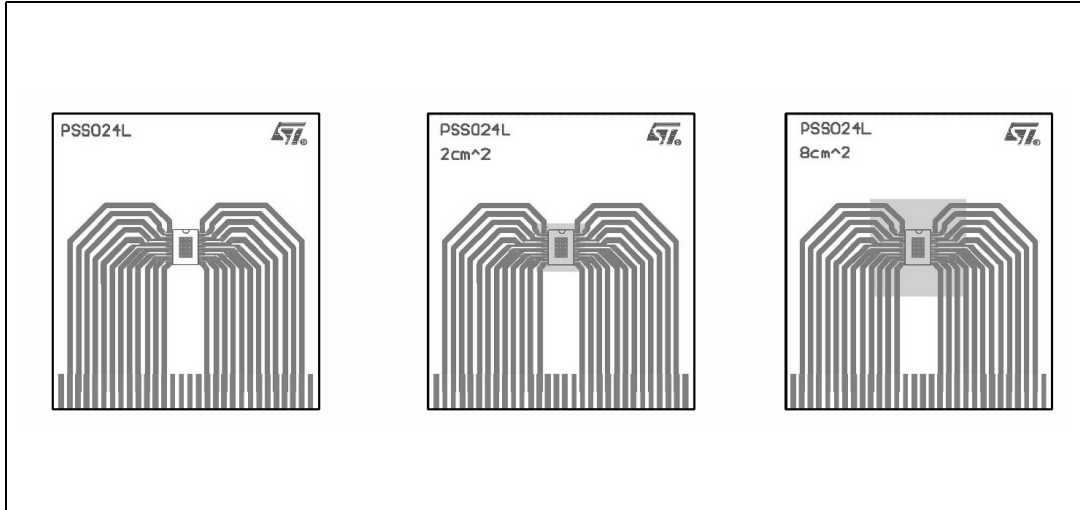
Figure 9. Charge pump switching frequency (typical) vs temperature



8 Package and PC board thermal data

8.1 VNI4140K thermal data

Figure 10. VNI4140K PC board



Note: Layout condition of R_{th} and Z_{th} measurements (PCB: Double layer, Thermal Vias, FR4 area = 77 mm x 86 mm, PCB thickness=1.6 mm, Cu thickness = 70 mm (front and back side), Copper areas: from minimum pad lay-out to 8 cm²).

Figure 11. R_{thJA} vs PCB copper area in open box free air condition (one channel ON)

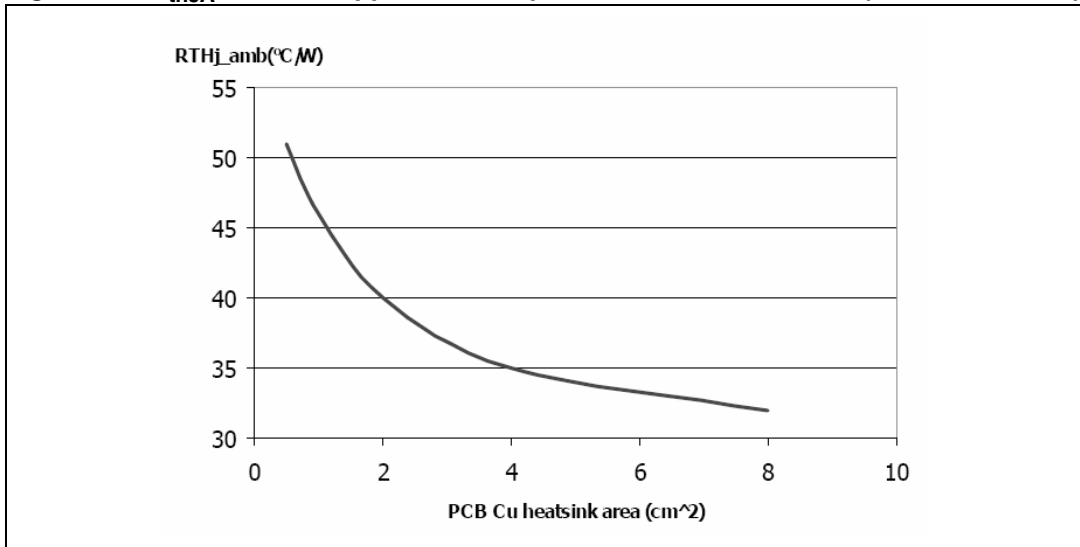
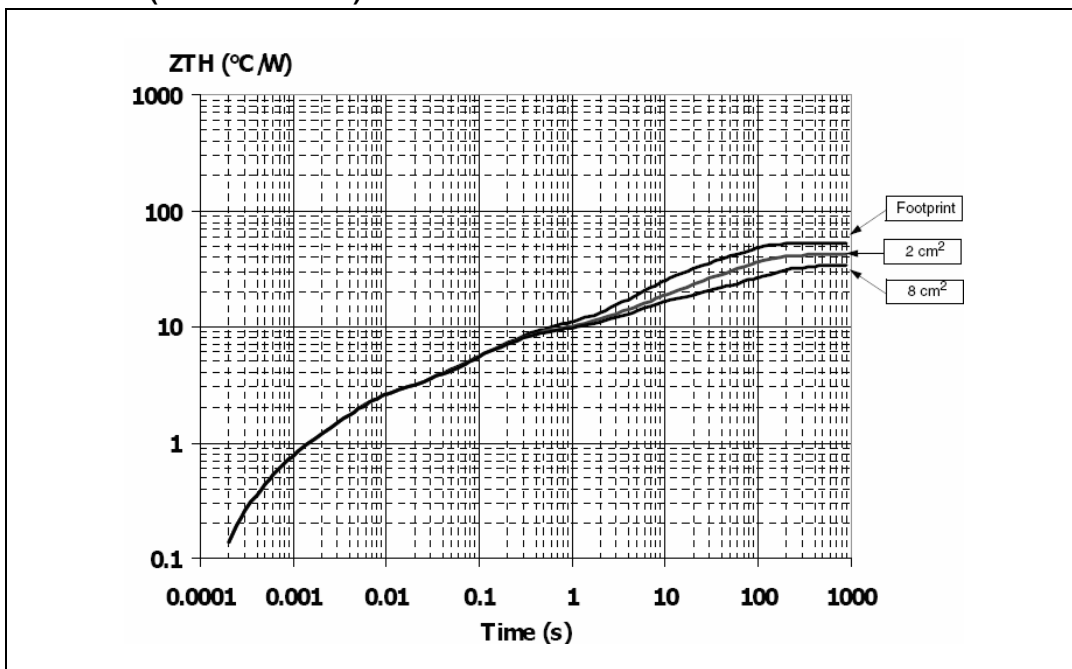


Figure 12. VNI4140K thermal impedance junction ambient single pulse (one channel on)



9 Reverse polarity protection

A schematic solution to protect the IC against a reverse polarity condition is proposed.

This schematic is effective with any type of load connected to the outputs of the IC.

The R_{GND} resistor value can be selected according to the following conditions to be met:

1. $R_{GND} \leq 600 \text{ mV} / (I_S \text{ in ON state max})$.
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

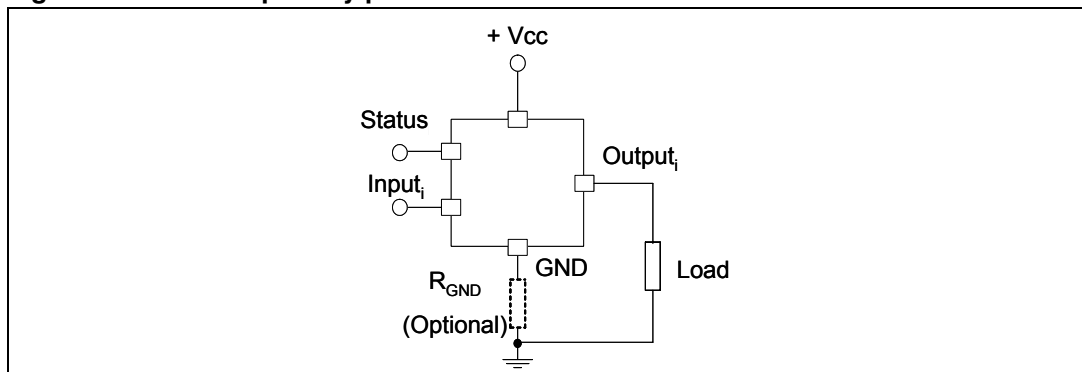
The power dissipation associated to R_{GND} during reverse polarity condition is:

$$PD = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared by several different ICs. In such case I_S value on formula (1) is the sum of the maximum ON-state currents of the different devices.

Please note that if the microprocessor ground and the device ground are separated then the voltage drop across the R_{GND} (given by I_S in ON state max * R_{GND}) produce a difference between the generated input level and the IC input signal level. This voltage drop will vary depending on how many devices are ON in the case of several high side switches sharing the same R_{GND} .

Figure 13. Reverse polarity protection



10 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK[®] packages. These packages have a lead-free second level interconnect. The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 9. PowerSSO-24™ mechanical data

Symbol	mm		
	Min	Typ	Max
A	2.15		2.47
A2	2.15		2.40
a1	0		0.075
b	0.33		0.51
c	0.23		0.32
D	10.10		10.50
E	7.4		7.6
e		0.8	
e3		8.8	
G			0.1
G1			0.06
H	10.1		10.5
h			0.4
L	0.55		0.85
N			10deg
X	4.1		4.7
Y	6.5		7.1

Figure 14. PowerSSO-24™ package dimensions

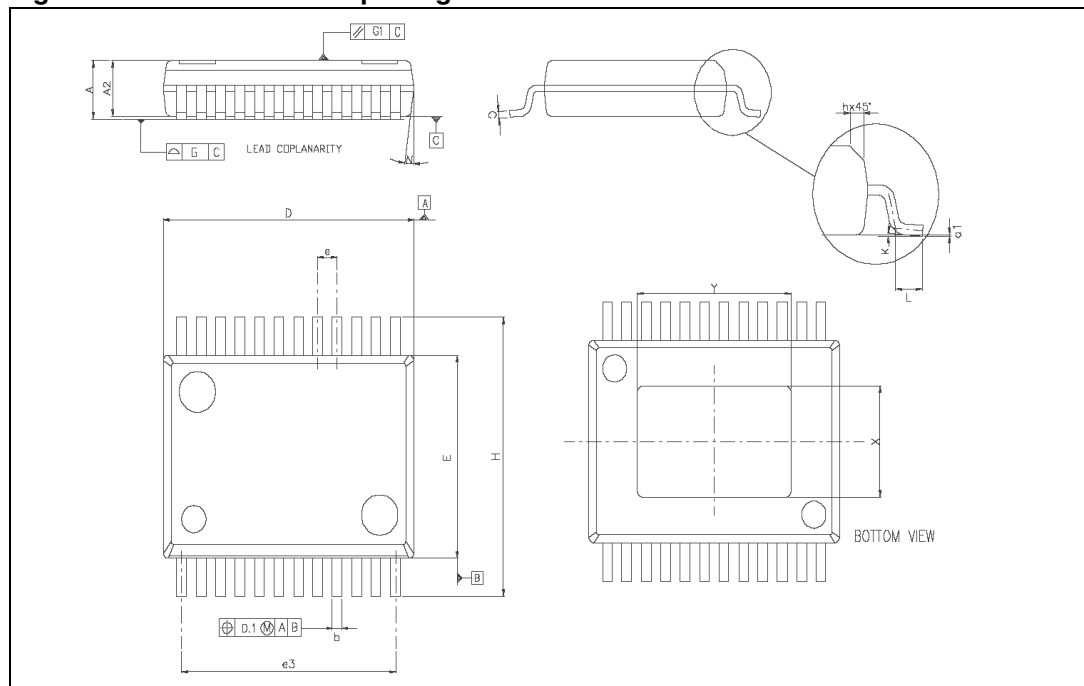


Figure 15. PowerSSO-24™ tube shipment (no suffix)

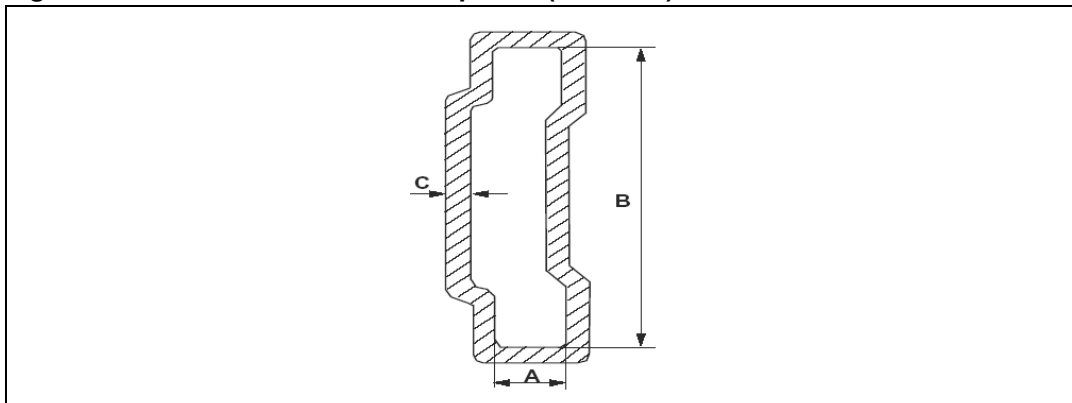


Table 10. PowerSSO-24™ tube shipment

Base quantity	49
Bulk quantity	1225
Tube length (± 0.5)	532
A	3.5
B	13.8
C (± 0.1)	0.6

Note: All dimensions are in mm.

Figure 16. PowerSSO-24™ reel shipment (suffix “TR”)

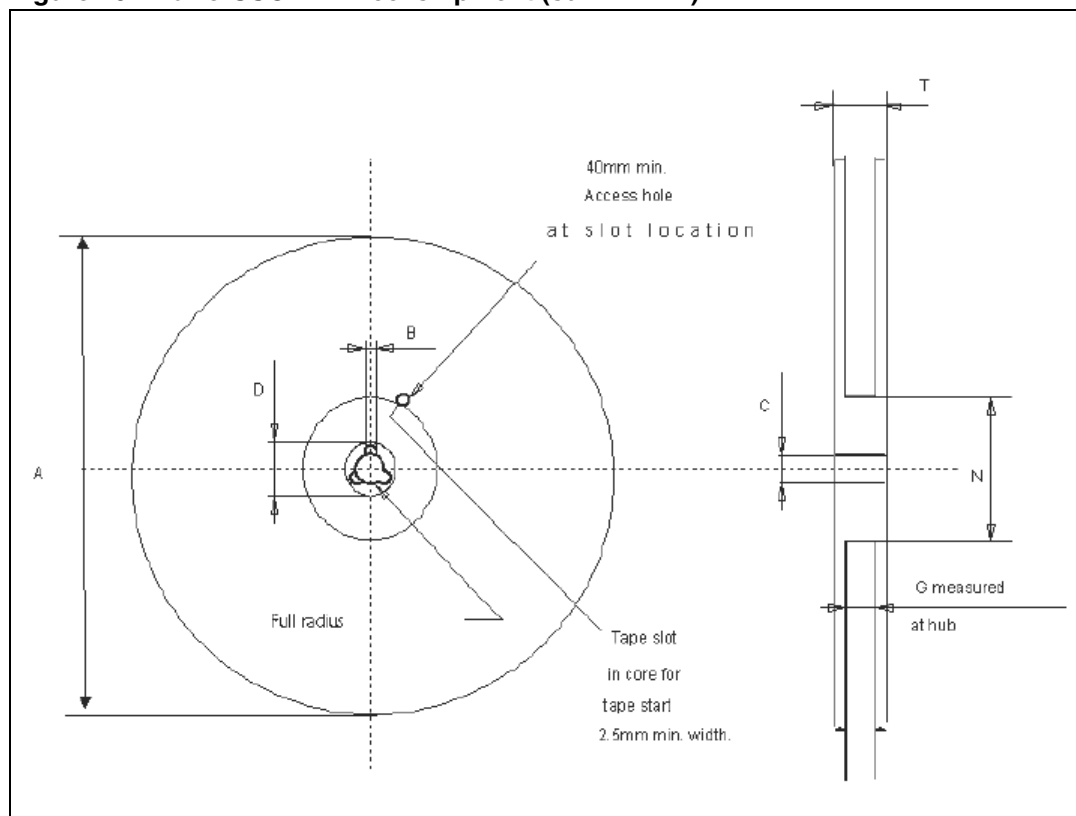


Table 11. PowerSSO-24™ reel dimensions

Base quantity	1000
Bulk quantity	1000
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (2 ± 0)	24.4
N (min)	100
T (max)	30.4

Figure 17. PowerSSO-24™ tape dimensions

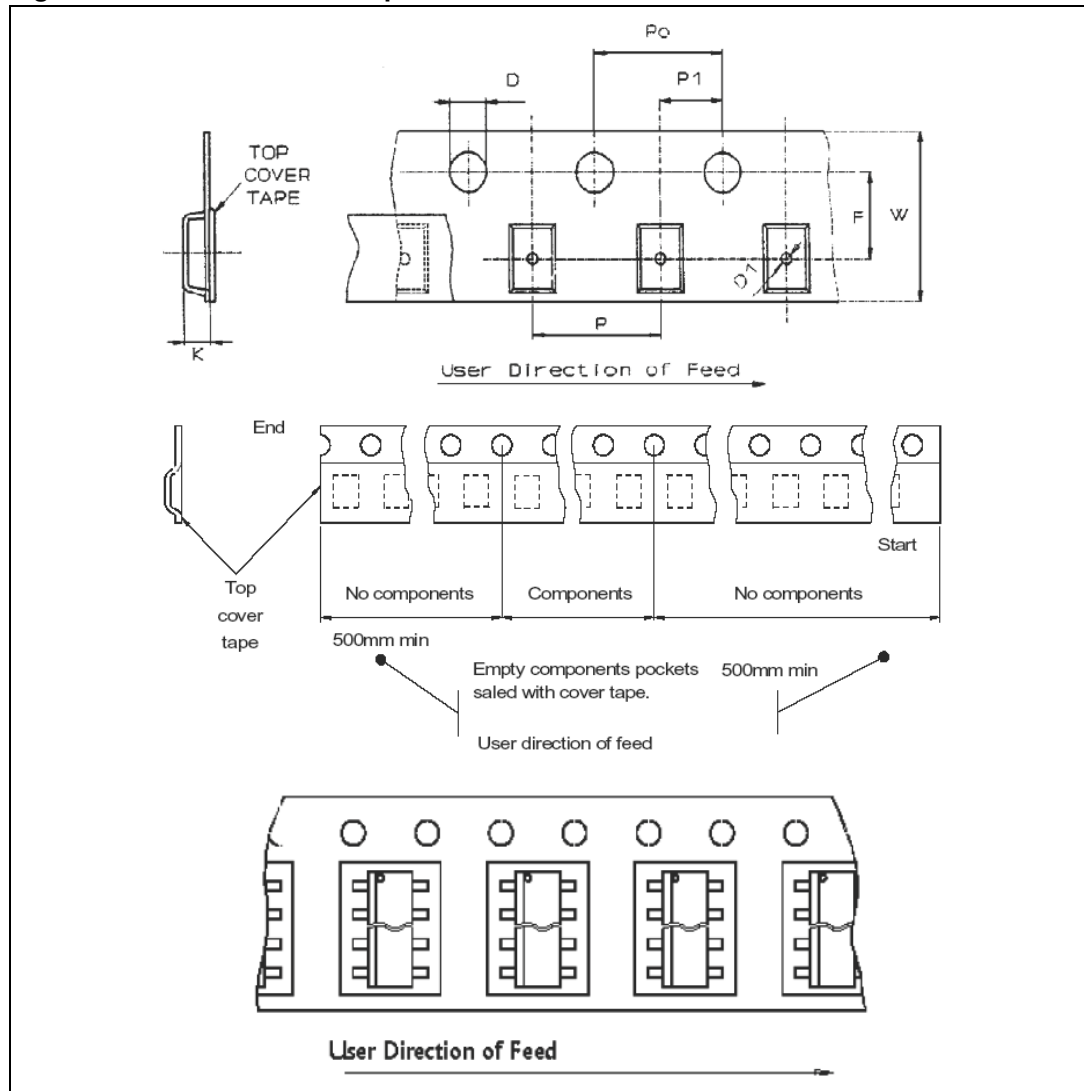


Table 12. PowerSSO-24™ tape dimensions

Tape width	W	24
Tape hole spacing	P0 (± 0.1)	4
Component spacing	P	12
Hole diameter	D (± 0.05)	1.55
Hole diameter	D1 (min)	1.5
Hole position	F (± 0.1)	11.5
Compartment depth	K (max)	2.85
Hole spacing	P1 (± 0.1)	2

Note: According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

11 Order codes

Table 13. Order codes

Order codes	Package	Packaging
VNI4140K	PowerSSO-24	Tube
VNI4140KTR	PowerSSO-24	Tape and reel

12 Revision history

Table 14. Document revision history

Date	Revision	Changes
16-Nov-2007	1	Initial release
26-Nov-2007	2	Updated electrical parameters values
08-Jul-2008	3	Inserted: <i>Figure 4 on page 9</i> and <i>Section 9: Reverse polarity protection on page 16</i>

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